

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 6,940,090 B2
DATED : September 6, 2005
INVENTOR(S) : Saito et al.

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

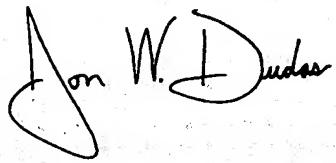
Title page, Item [54] and Column 1, lines 1-3,

Title, should read:

**-- [54] A WIDEBAND GAP POWER SEMICONDUCTOR DEVICE HAVING A
LOW ON-RESISTANCE AND HAVING A HIGH AVALANCHE CAPABILITY
USED FOR POWER CONTROL. --**

Signed and Sealed this

Thirteenth Day of December, 2005



JON W. DUDAS
Director of the United States Patent and Trademark Office